NSN 5961-00-119-8820

Diode Semiconductor Device - Page 1 of 2



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Inclosure Material:
Metal
Overall Length: 1.453 inches
Overall Diameter:
0.667 inches
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case Overall Width Across Flats:
Between 0.667 inches and 0.687 inches Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
20.0 regulator voltage
Voltage Tolerance In Percent:
-5.0 to 5.0
Current Rating Per Characteristic:
630.00 milliamperes source cutoff current horsepower metric and 2.38 amperes dc current in reverse breakdown region
Power Rating Per Characteristic:
50.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius case
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 1 tab, solder lug
Specification Data:
81349-mil-s-19500/358 government specification
Shelf Life:
N/a

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Unit Of Measure:

NSN 5961-00-119-8820

Diode Semiconductor Device - Page 2 of 2



Demilitarization:

No

Fiig:

A110a0